

**DUAL P-CHANNEL ENHANCEMENT MODE MOSFET**
**Product Summary**

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> Max         | I <sub>D</sub> Max<br>T <sub>A</sub> = +25°C |
|-------------------|---------------------------------|--|
| -20V              | 75mΩ @ V <sub>GS</sub> = -4.5V  | -3.8A  |
|                   | 137mΩ @ V <sub>GS</sub> = -2.5V | -3.0A  |

**Description**

This MOSFET is designed to minimize on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

**Applications**

- Load Switch
- Power Management Functions
- Portable Power Adaptors

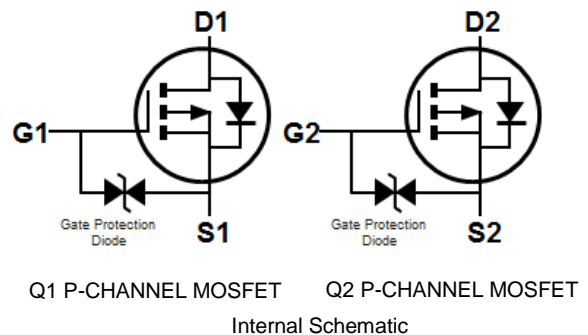
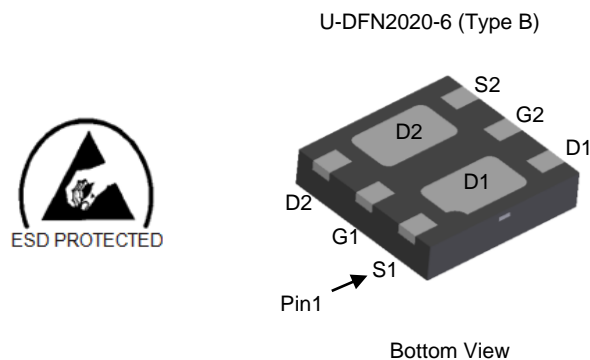
**Features**

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.**

<https://www.diodes.com/quality/product-definitions/>

**Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 <sup>(e4)</sup>
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)


**Ordering Information** (Note 4)

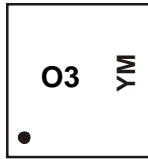
| Part Number     | Case                 | Packaging          |
|-----------------|----------------------|--------------------|
| DMP2075UFDB -7  | U-DFN2020-6 (Type B) | 3,000/Tape & Reel  |
| DMP2075UFDB -13 | U-DFN2020-6 (Type B) | 10,000/Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information

Site 1

U-DFN2020-6 (Type B)



O3 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: H = 2020)  
 M = Month (ex: 9 = September)

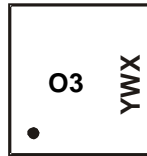
Date Code Key

| Year | 2017 | ... | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 |
|------|------|-----|------|------|------|------|------|------|------|------|------|------|
| Code | E    | ... | H    | I    | J    | K    | L    | M    | N    | O    | P    | R    |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code  | 1   | 2   | 3   | 4   | 5   | 6   | 7   | 8   | 9   | O   | N   | D   |

Site 2



O3 = Product Type Marking Code  
 YWX = Date Code Marking  
 Y = Year (ex: 0 = 2020)  
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)  
 X = Internal Code (ex: U = Monday)

Date Code Key

| Year | 2017 | ... | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 |
|------|------|-----|------|------|------|------|------|------|------|------|------|------|
| Code | 7    | ... | 0    | 1    | 2    | 3    | 4    | 5    | 6    | 7    | 8    | 9    |

| Week | 1-26 | 27-52 | 53 |
|------|------|-------|----|
| Code | A-Z  | a-z   | z  |

| Internal Code | Sun | Mon | Tue | Wed | Thu | Fri | Sat |
|---------------|-----|-----|-----|-----|-----|-----|-----|
| Code          | T   | U   | V   | W   | X   | Y   | Z   |

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic  |              |  | Symbol           | Value        | Unit |
|---|--------------|--|------------------|--------------|------|
| Drain-Source Voltage                                      |              |  | V <sub>DSS</sub> | -20          | V    |
| Gate-Source Voltage                                       |              |  | V <sub>GSS</sub> | ±8           | V    |
| Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V | Steady State | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | I <sub>D</sub>   | -3.8<br>-3.0 | A    |
| Maximum Continuous Body Diode Forward Current (Note 5)    |              |  | I <sub>S</sub>   | -1.0         | A    |
| Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)        |              |  | I <sub>DM</sub>  | -25          | A    |
| Avalanche Current (Note 7) L = 0.1mH                      |              |  | I <sub>AS</sub>  | -13          | A    |
| Avalanche Energy (Note 7) L = 0.1mH                       |              |  | E <sub>AS</sub>  | 8.5          | mJ   |

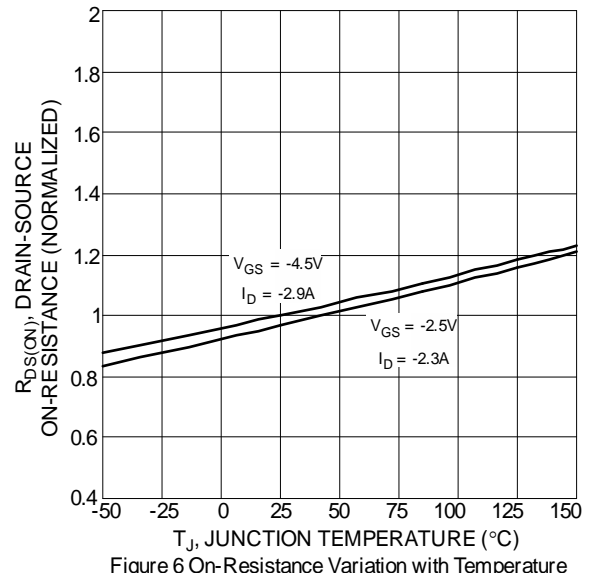
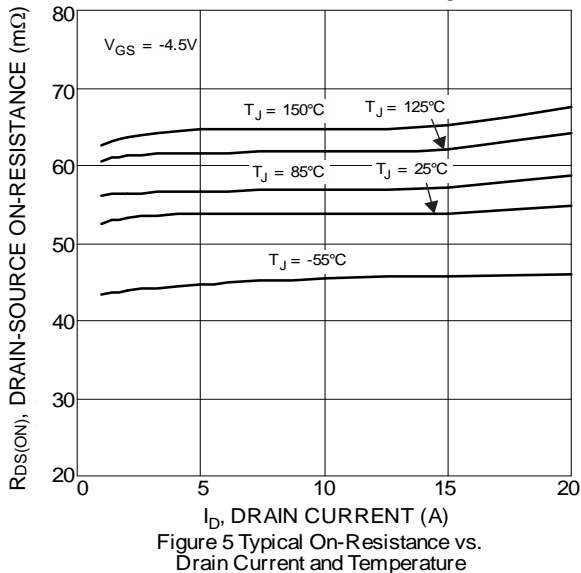
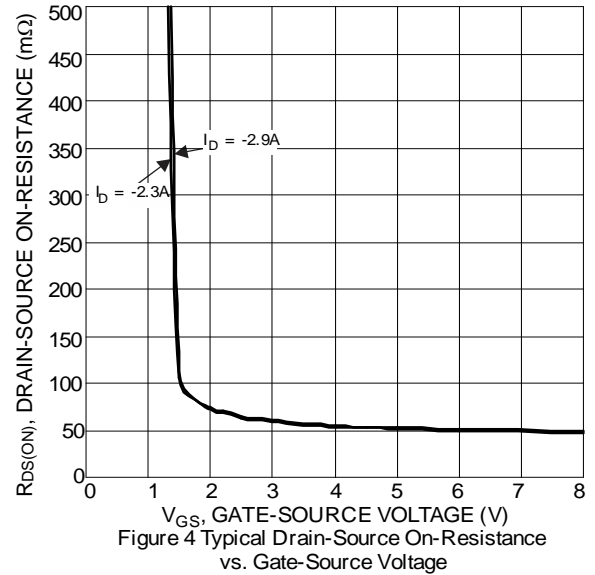
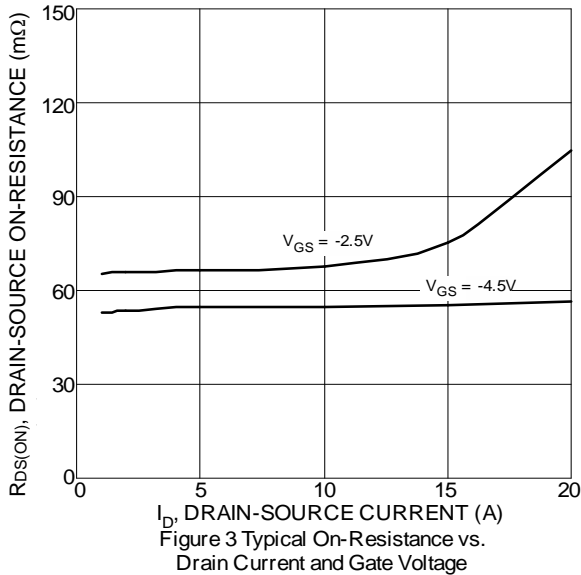
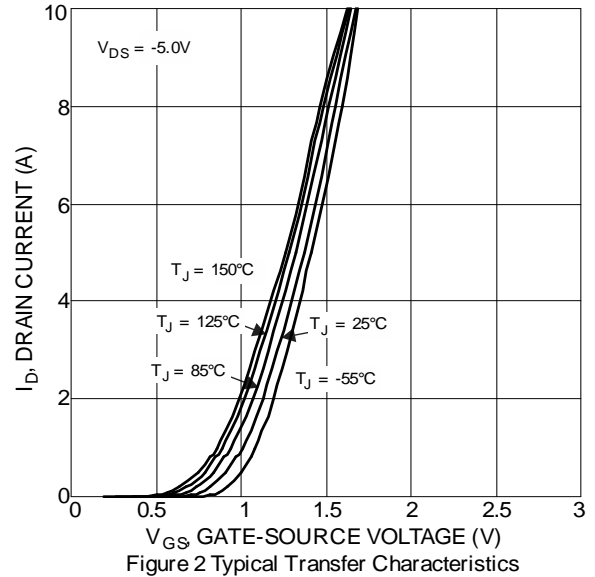
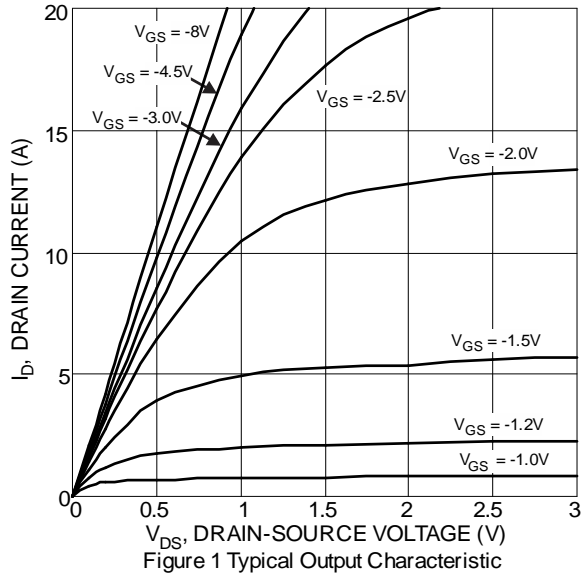
**Thermal Characteristics**

| Characteristic                                   |                        | Symbol                            | Value       | Unit |
|--|------------------------|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5)                 | T <sub>A</sub> = +25°C | P <sub>D</sub>                    | 0.7         | W    |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State           | R <sub>θJA</sub>                  | 178         | °C/W |
| Total Power Dissipation (Note 6)                 | T <sub>A</sub> = +25°C | P <sub>D</sub>                    | 1.4         | W    |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State           | R <sub>θJA</sub>                  | 92          | °C/W |
| Thermal Resistance, Junction to Case (Note 6)    |                        | R <sub>θJC</sub>                  | 22          |      |
| Operating and Storage Temperature Range          |                        | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic   | Symbol              | Min   | Typ  | Max  | Unit | Test Condition   |
|--|---------------------|-------|------|------|------|--|
| <b>OFF CHARACTERISTICS</b> (Note 8)                    |                     |       |      |      |      |  |
| Drain-Source Breakdown Voltage                         | BV <sub>DSS</sub>   | -20   | —    | —    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA  |
| Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C | I <sub>DSS</sub>    | —     | —    | -1.0 | μA   | V <sub>D</sub> = -20V, V <sub>GS</sub> = 0V  |
| Gate-Source Leakage                                    | I <sub>GSS</sub>    | —     | —    | ±10  | μA   | V <sub>GS</sub> = ±6.4V, V <sub>D</sub> = 0V   |
| <b>ON CHARACTERISTICS</b> (Note 8)                     |                     |       |      |      |      |  |
| Gate Threshold Voltage                                 | V <sub>GS(TH)</sub> | -0.35 | —    | -1.4 | V    | V <sub>D</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA                                     |
| Static Drain-Source On-Resistance                      | R <sub>DS(ON)</sub> | —     | 53   | 75   | mΩ   | V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.9A  |
|  |                     | —     | 64   | 137  |      | V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2.3A  |
| Diode Forward Voltage                                  | V <sub>SD</sub>     | —     | -0.7 | -1.2 | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = -3.0A   |
| <b>DYNAMIC CHARACTERISTICS</b> (Note 9)                |                     |       |      |      |      |  |
| Input Capacitance                                      | C <sub>iss</sub>    | —     | 642  | —    | pF   | V <sub>D</sub> = -10V, V <sub>GS</sub> = 0V,<br>f = 1.0MHz                                     |
| Output Capacitance                                     | C <sub>oss</sub>    | —     | 98   | —    | pF   |  |
| Reverse Transfer Capacitance                           | C <sub>rss</sub>    | —     | 87   | —    | pF   |  |
| Gate Resistance  | R <sub>g</sub>      | —     | 26.5 | —    | Ω    | V <sub>D</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz  |
| Total Gate Charge (V <sub>GS</sub> = -4.5V)            | Q <sub>g</sub>      | —     | 8.8  | —    | nC   | V <sub>D</sub> = -10V, I <sub>D</sub> = -3.7A  |
| Total Gate Charge (V <sub>GS</sub> = -8V)              |                     | —     | 15   | —    | nC   |  |
| Gate-Source Charge                                     | Q <sub>gs</sub>     | —     | 0.9  | —    | nC   |  |
| Gate-Drain Charge                                      | Q <sub>gd</sub>     | —     | 2.9  | —    | nC   |  |
| Turn-On Delay Time                                     | t <sub>D(ON)</sub>  | —     | 5.5  | —    | ns   | V <sub>DD</sub> = -10V, V <sub>GS</sub> = -4.5V,<br>R <sub>L</sub> = 3.3Ω, R <sub>g</sub> = 1Ω |
| Turn-On Rise Time                                      | t <sub>R</sub>      | —     | 22.6 | —    | ns   |  |
| Turn-Off Delay Time                                    | t <sub>D(OFF)</sub> | —     | 34.1 | —    | ns   |  |
| Turn-Off Fall Time                                     | t <sub>F</sub>      | —     | 34.3 | —    | ns   |  |
| Body Diode Reverse Recovery Time                       | t <sub>RR</sub>     | —     | 13   | —    | ns   | I <sub>S</sub> = -3.0A, dI/dt = 100A/μs  |
| Body Diode Reverse Recovery Charge                     | Q <sub>RR</sub>     | —     | 3.3  | —    | nC   | I <sub>S</sub> = -3.0A, dI/dt = 100A/μs  |

- Notes: 5. Device mounted on FR-4 PCB board, with minimum recommended pad layout, single sided  
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.  
7. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.  
8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to product testing.



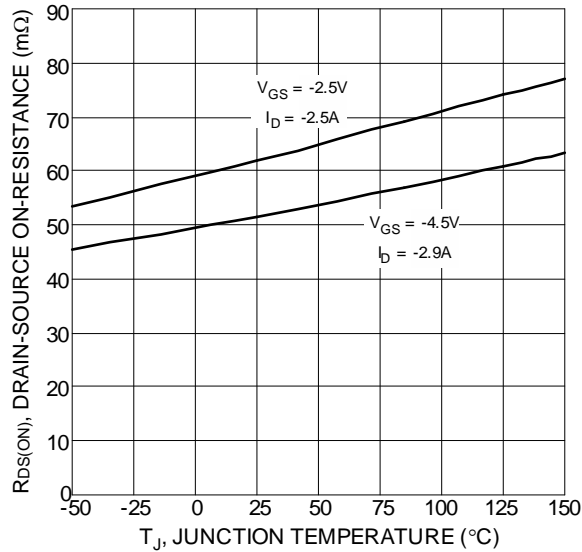


Figure 7 On-Resistance Variation with Temperature

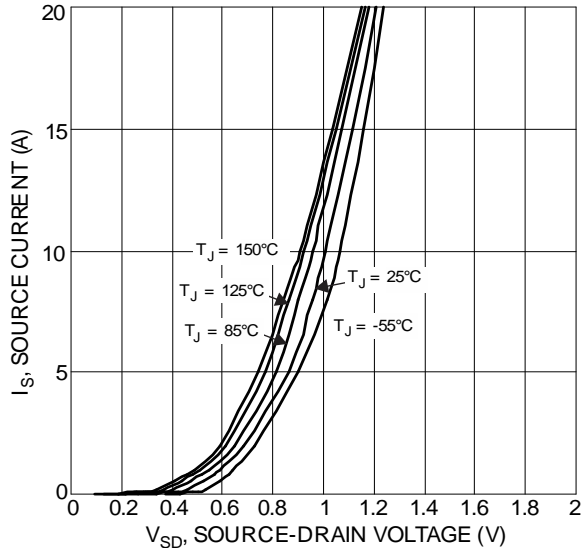


Figure 9 Diode Forward Voltage vs. Current

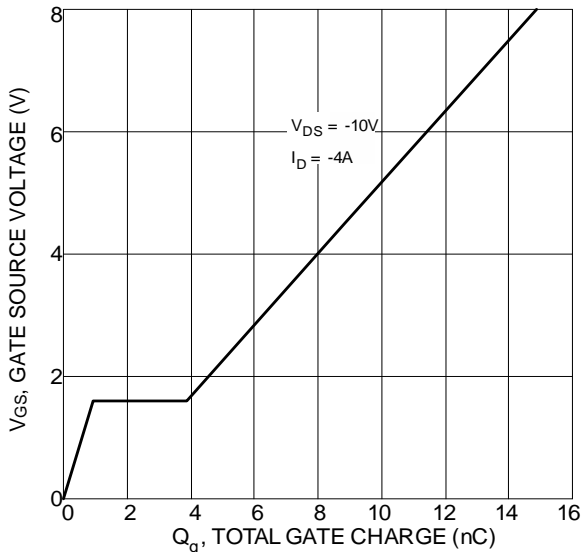


Figure 11 Gate Charge

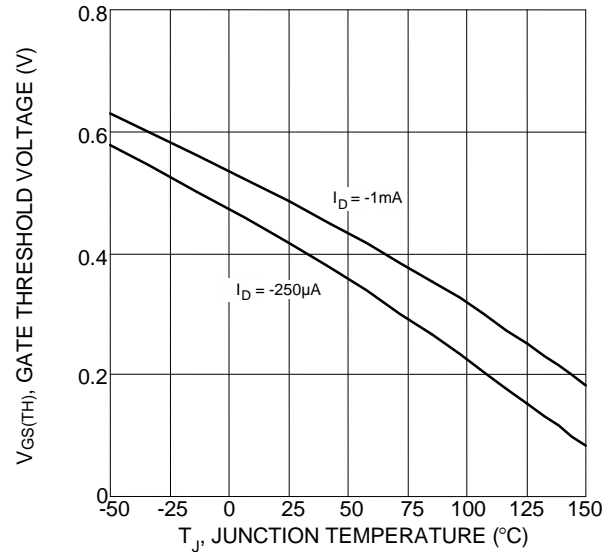


Figure 8 Gate Threshold Variation vs. Junction Temperature

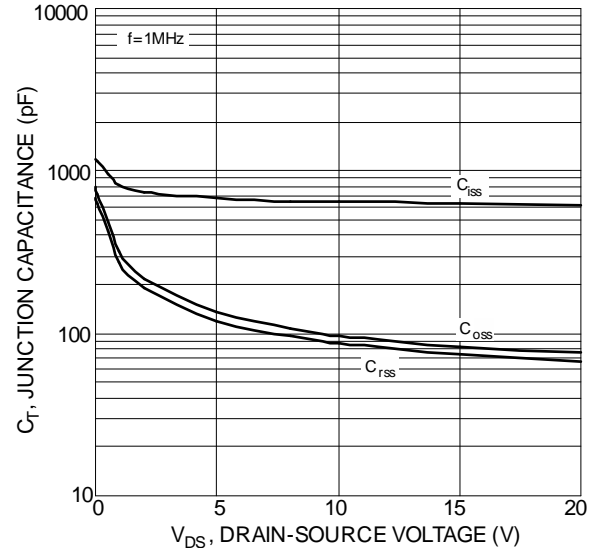


Figure 10 Typical Junction Capacitance

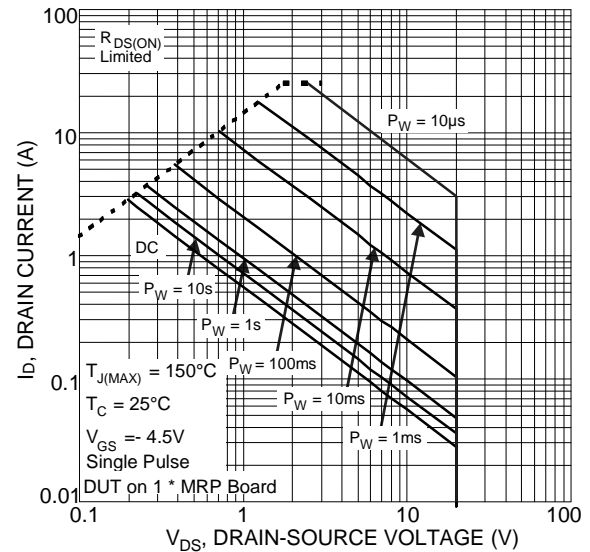
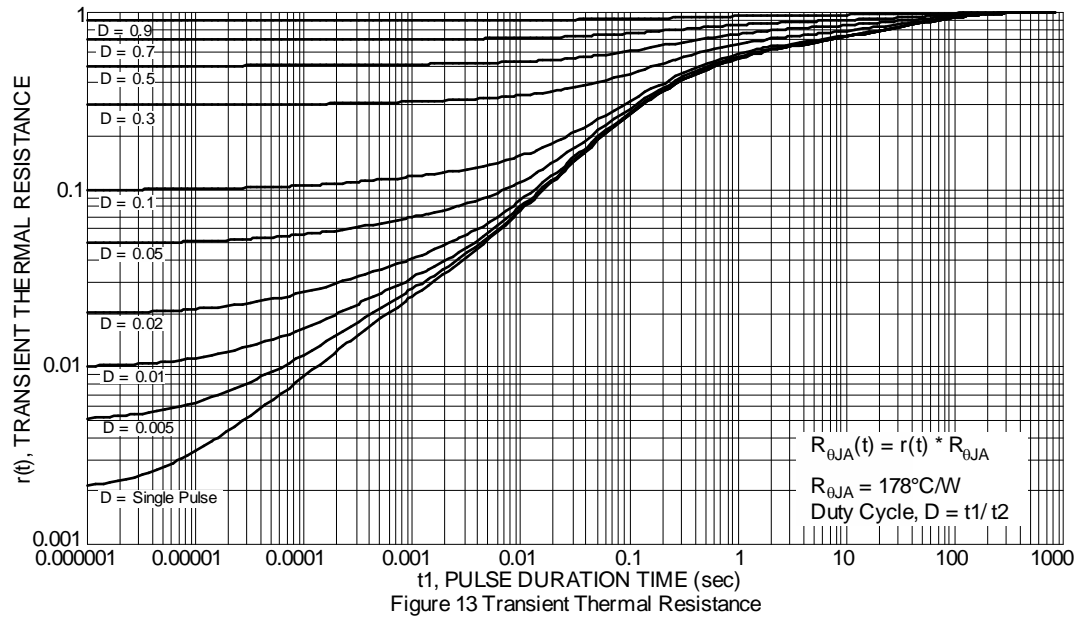


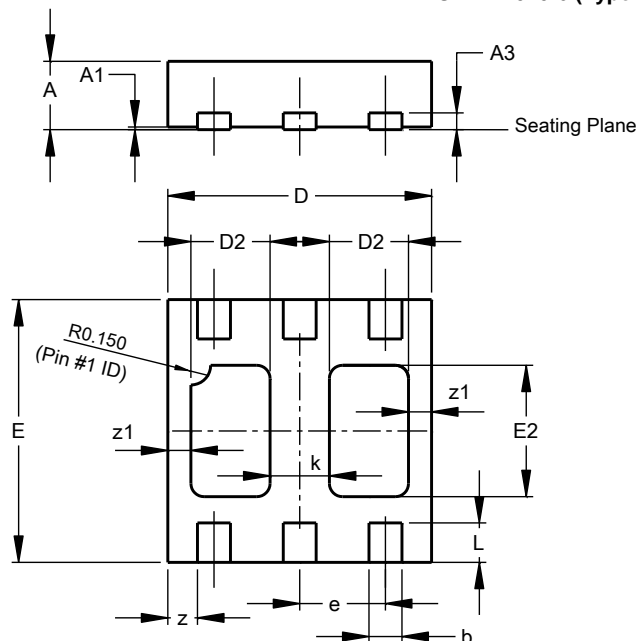
Figure 12 SOA, Safe Operation Area



## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type B)**

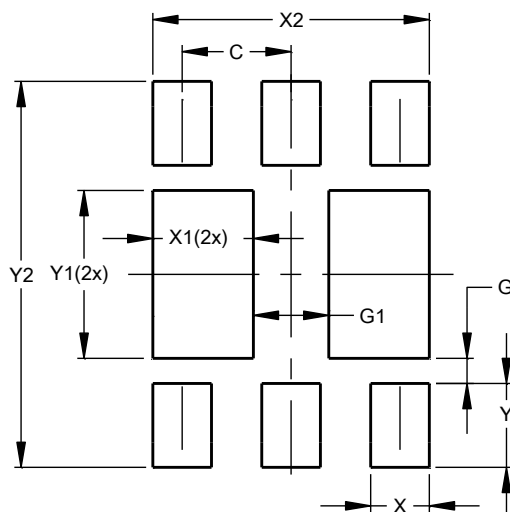


| U-DFN2020-6<br>(Type B) |       |       |       |
|-------------------------|-------|-------|-------|
| Dim                     | Min   | Max   | Typ   |
| A                       | 0.545 | 0.605 | 0.575 |
| A1                      | 0.00  | 0.05  | 0.02  |
| A3                      | -     | -     | 0.13  |
| b                       | 0.20  | 0.30  | 0.25  |
| D                       | 1.95  | 2.075 | 2.00  |
| D2                      | 0.50  | 0.70  | 0.60  |
| e                       | -     | -     | 0.65  |
| E                       | 1.95  | 2.075 | 2.00  |
| E2                      | 0.90  | 1.10  | 1.00  |
| k                       | -     | -     | 0.45  |
| L                       | 0.25  | 0.35  | 0.30  |
| z                       | -     | -     | 0.225 |
| z1                      | -     | -     | 0.175 |
| All Dimensions in mm    |       |       |       |

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type B)**



| Dimensions | Value<br>(in mm) |
|------------|------------------|
| C          | 0.650            |
| G          | 0.150            |
| G1         | 0.450            |
| X          | 0.350            |
| X1         | 0.600            |
| X2         | 1.650            |
| Y          | 0.500            |
| Y1         | 1.000            |
| Y2         | 2.300            |

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